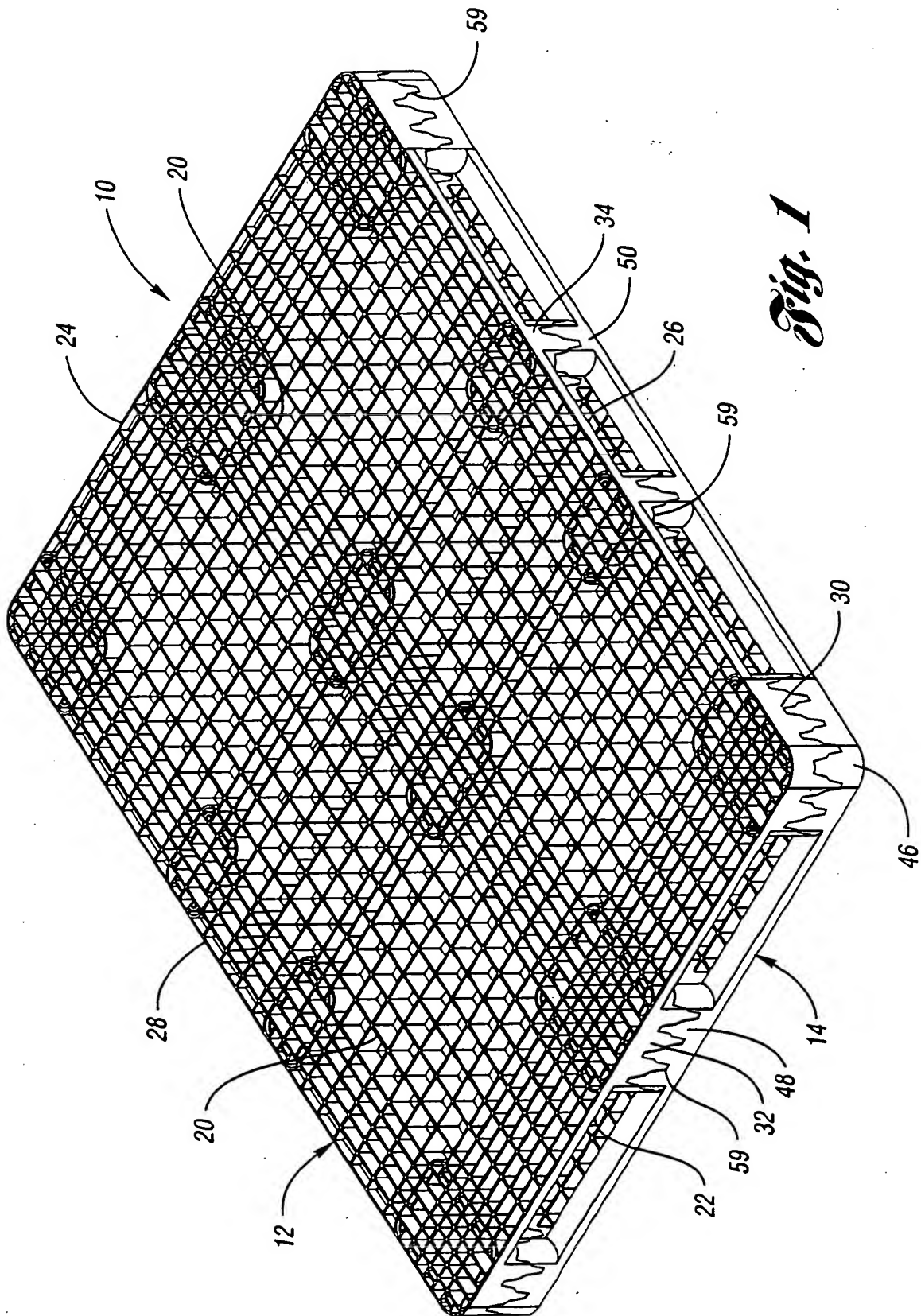


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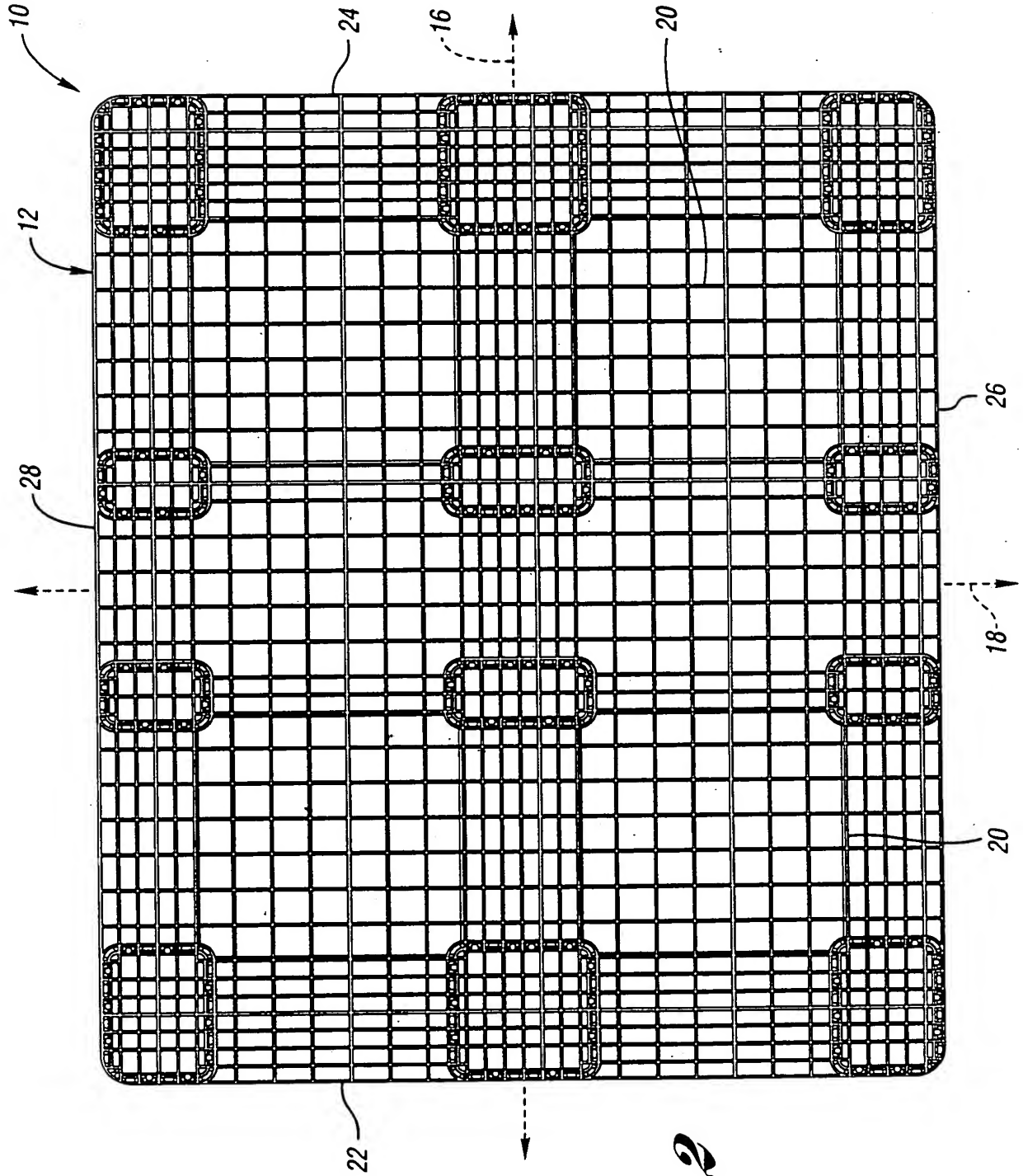


Fig. 2

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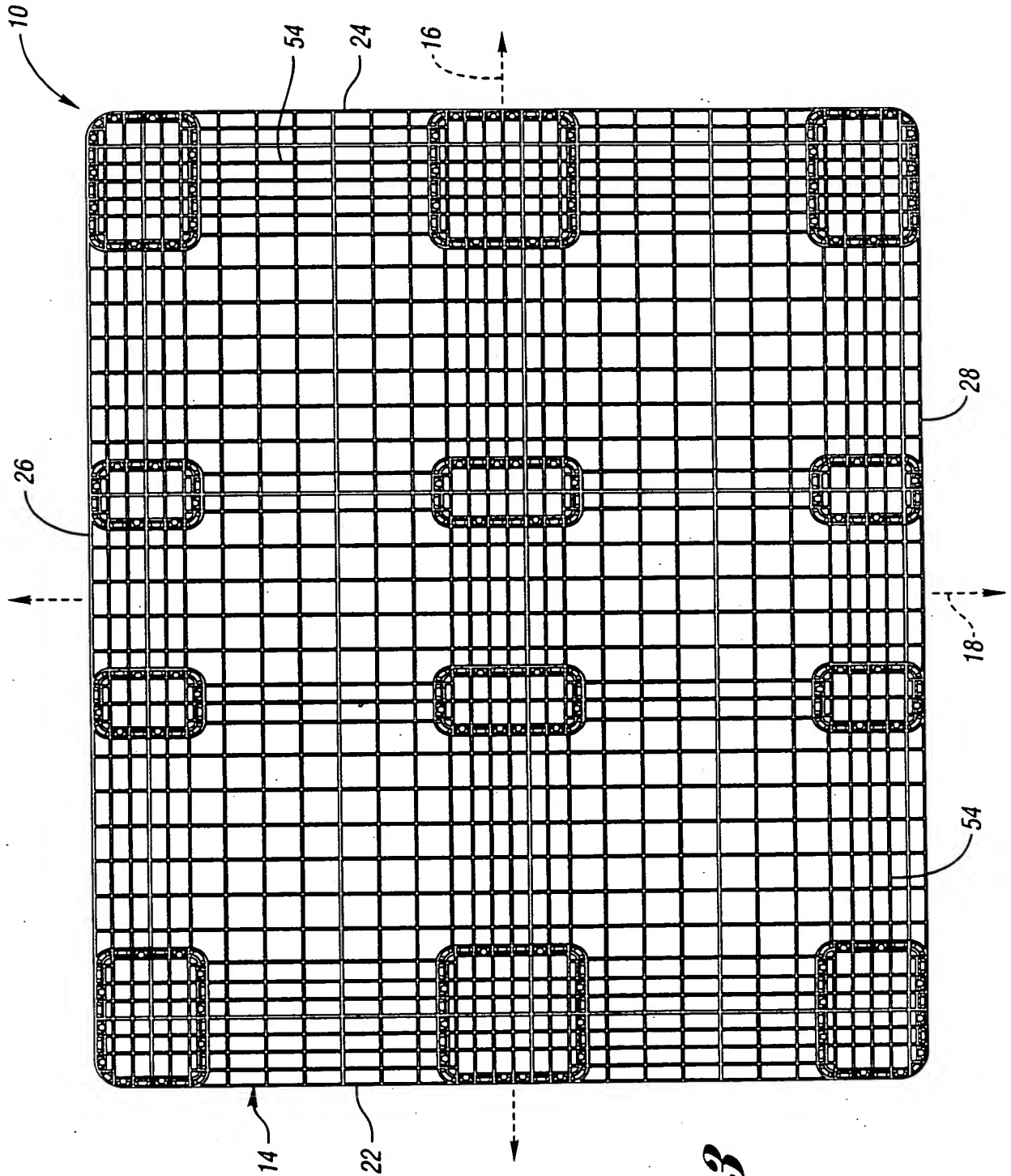
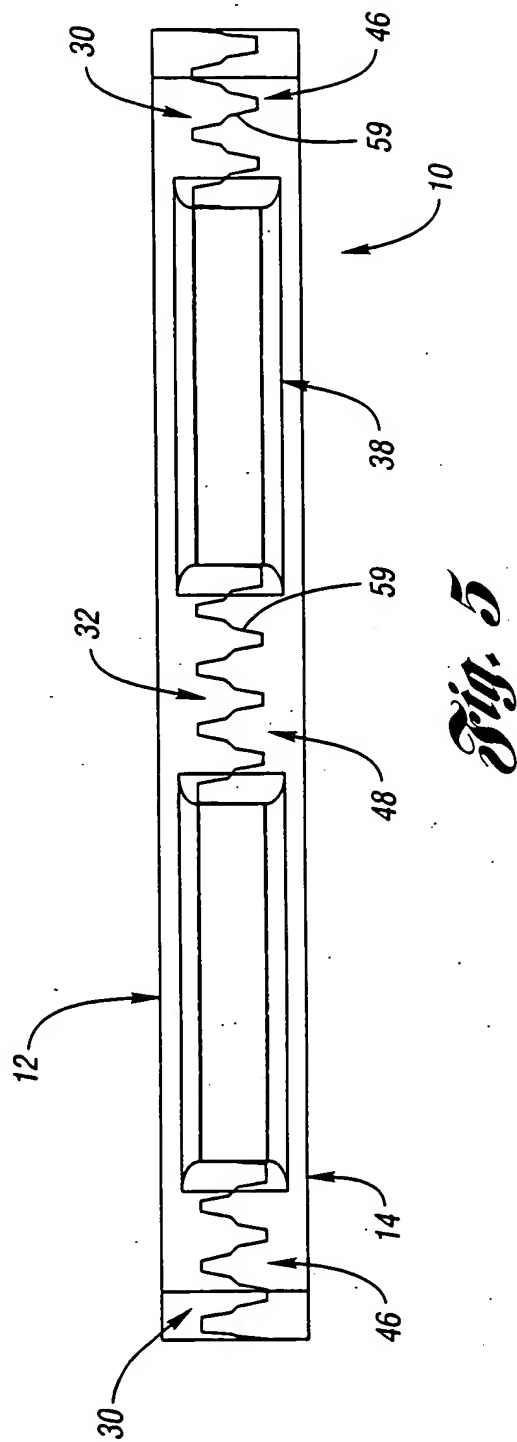
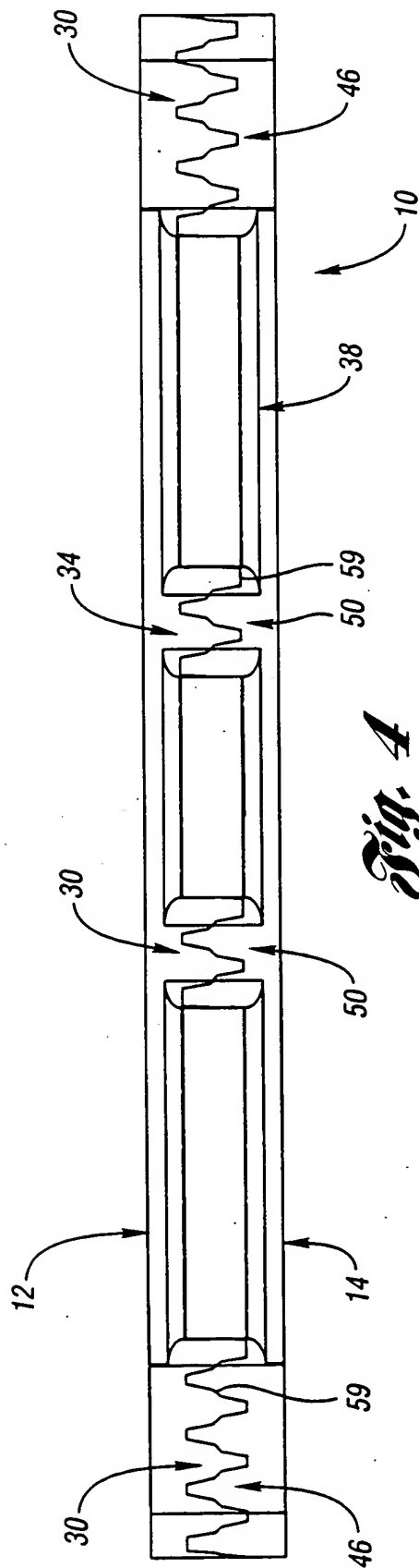
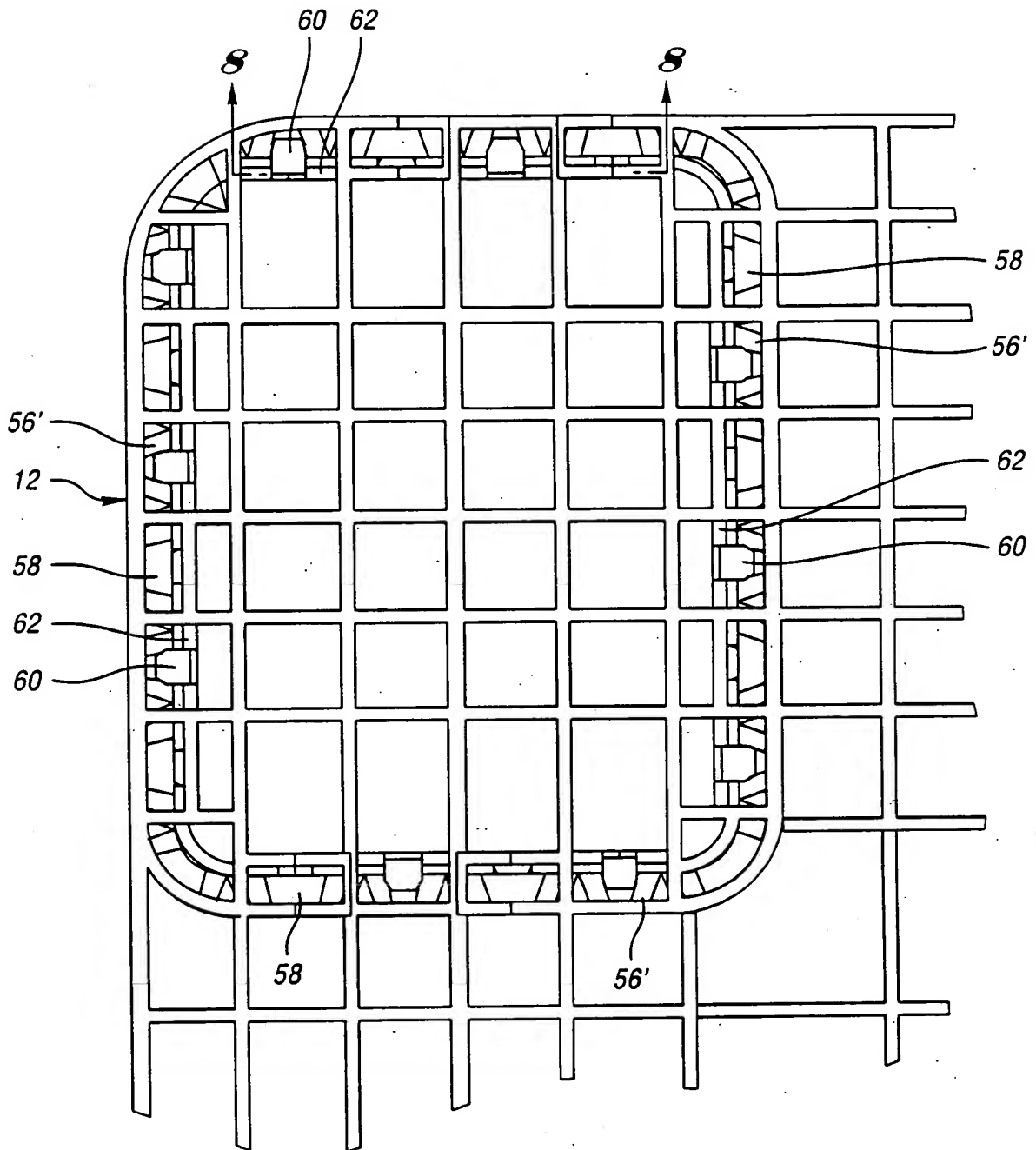


Fig. 3



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*Fig. 6*

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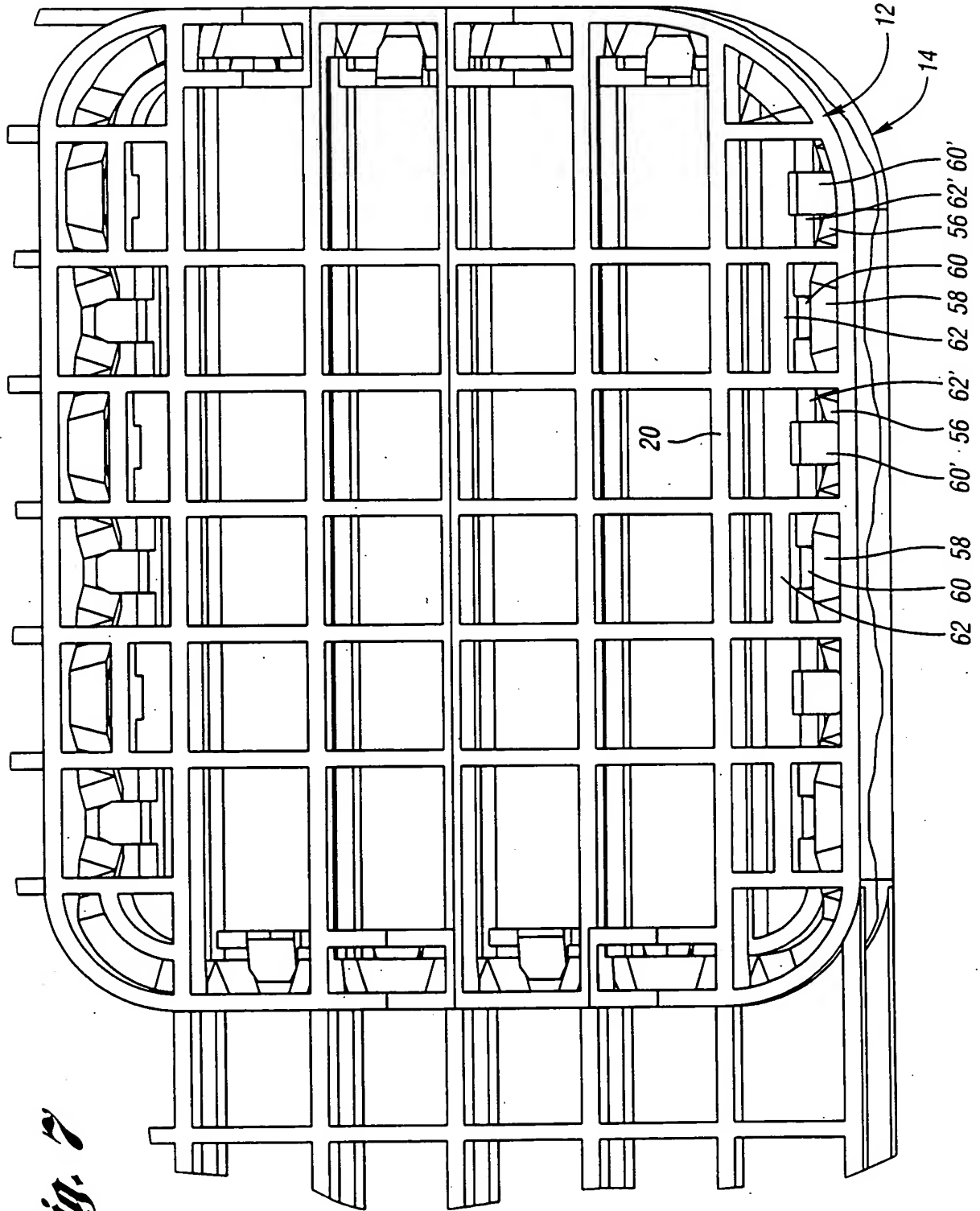
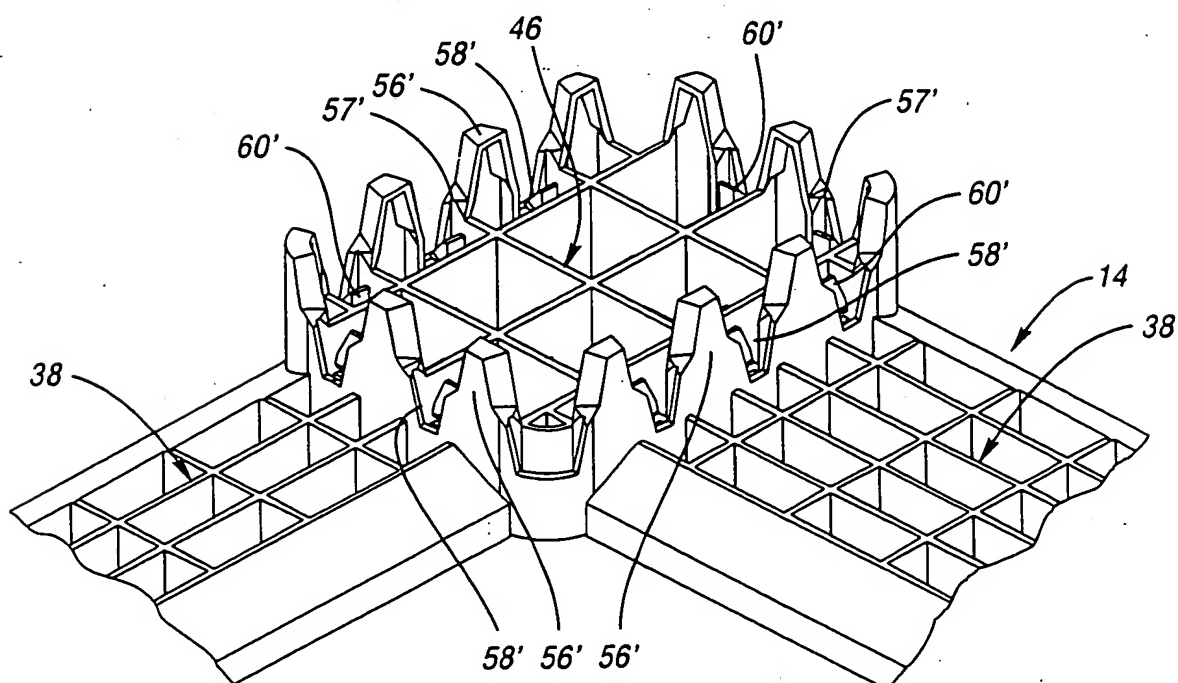


Fig. 2

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A cross-sectional diagram of a semiconductor device. The substrate consists of alternating vertical layers labeled 60 and 62. Layer 60 has diagonal hatching sloping down from left to right, while layer 62 has diagonal hatching sloping up from left to right. A thin layer 56 is deposited over the entire surface. On top of layer 56, there are several rectangular structures. Some of these structures have a central core labeled 56' which extends through the 56 layer into the underlying substrate. Other structures are smaller and do not contain a core. The labels 62', 60', and 56' are positioned at the bottom of the diagram, corresponding to the respective layers or features.

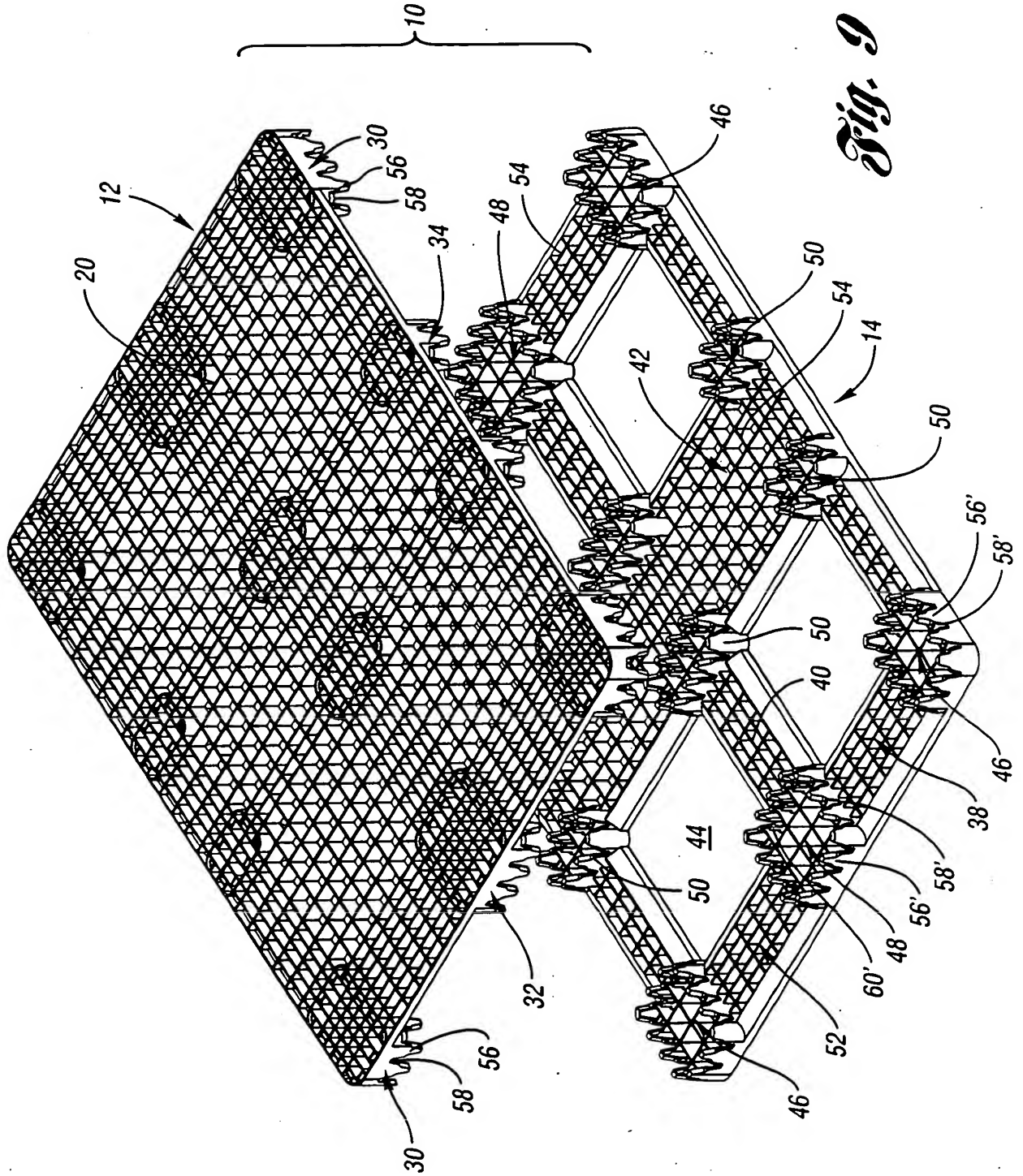
*Fig. 9*



*Fig. 14*

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*Fig. 9*

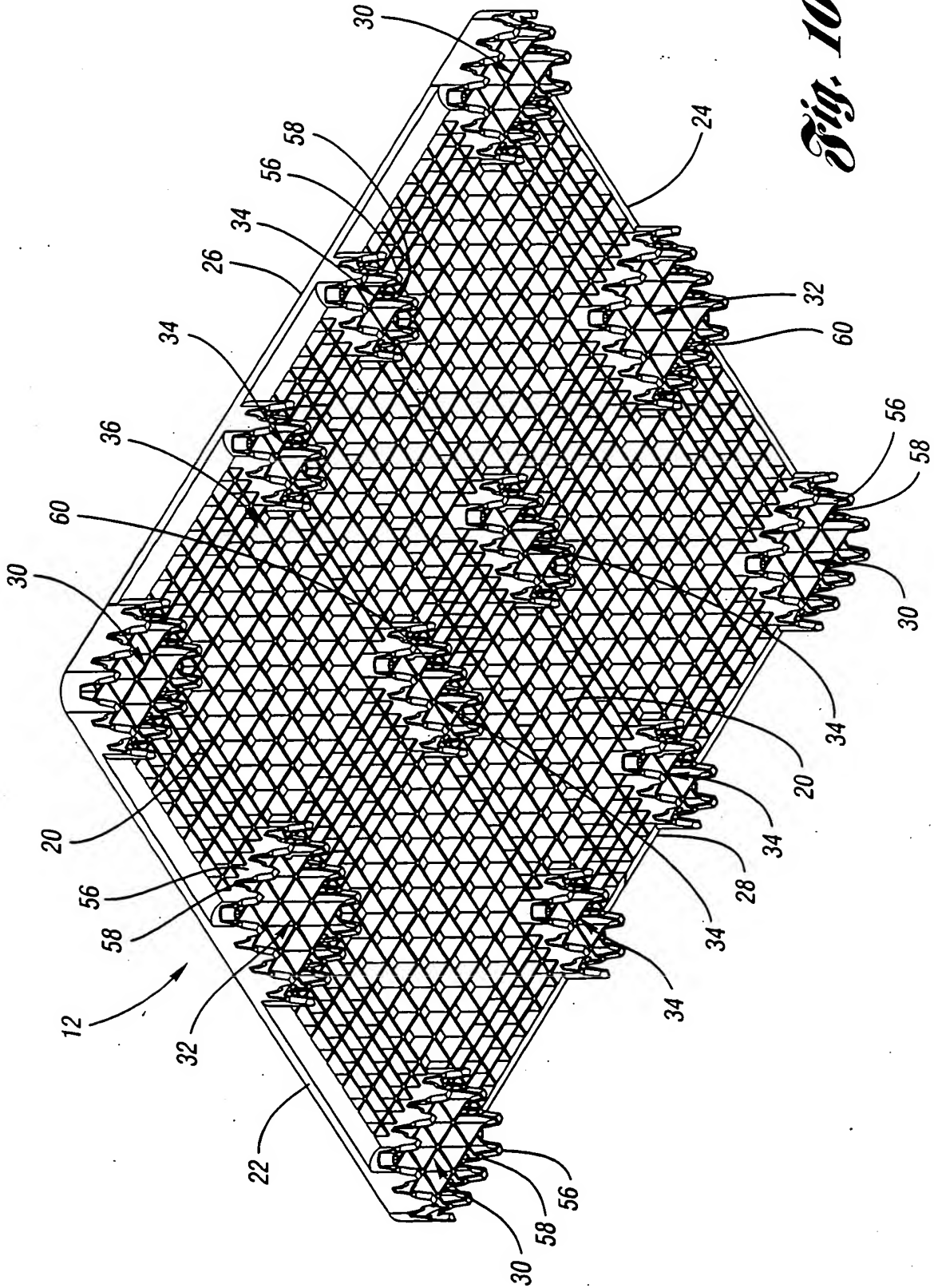


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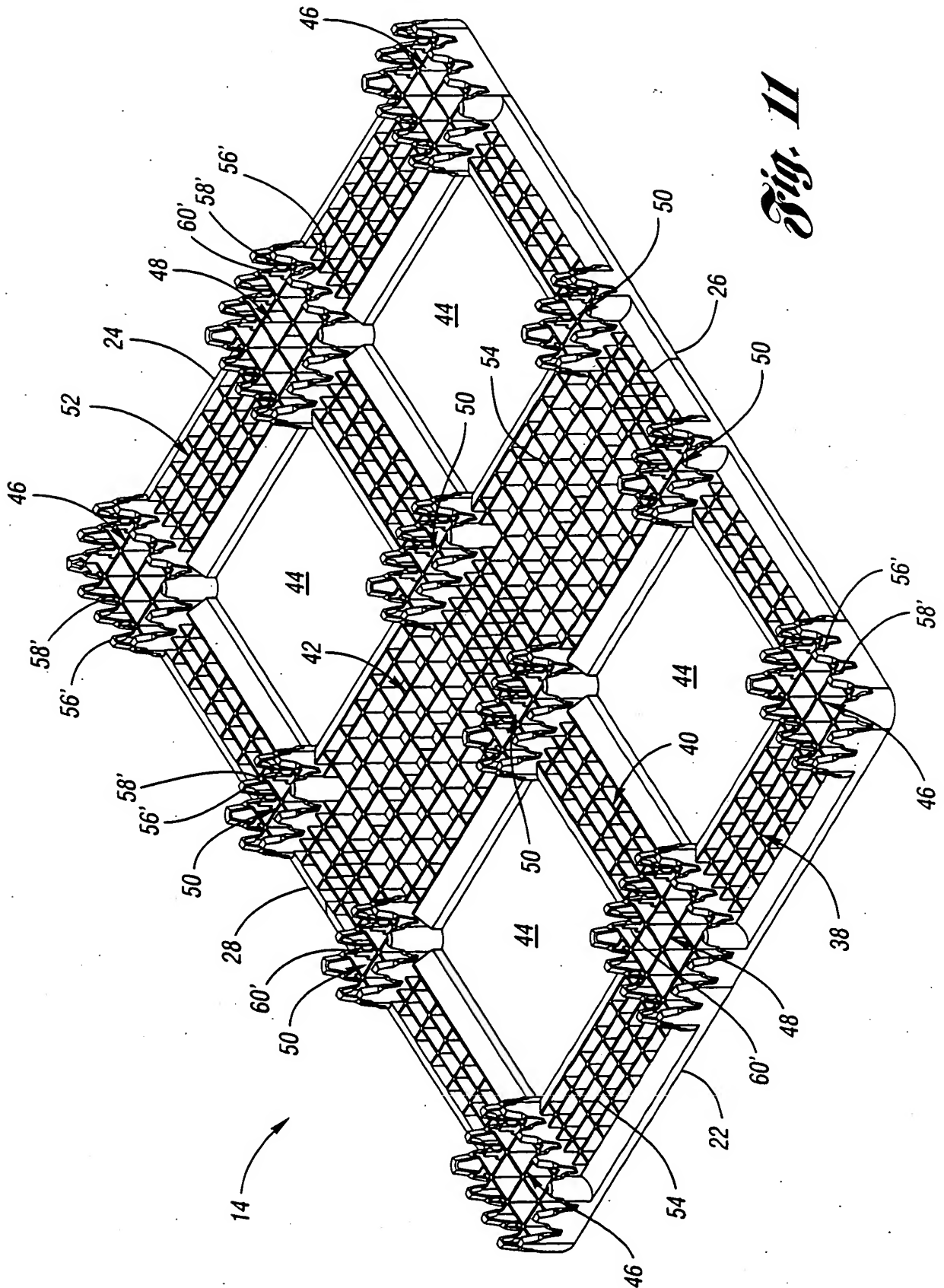
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*Fig. 10*



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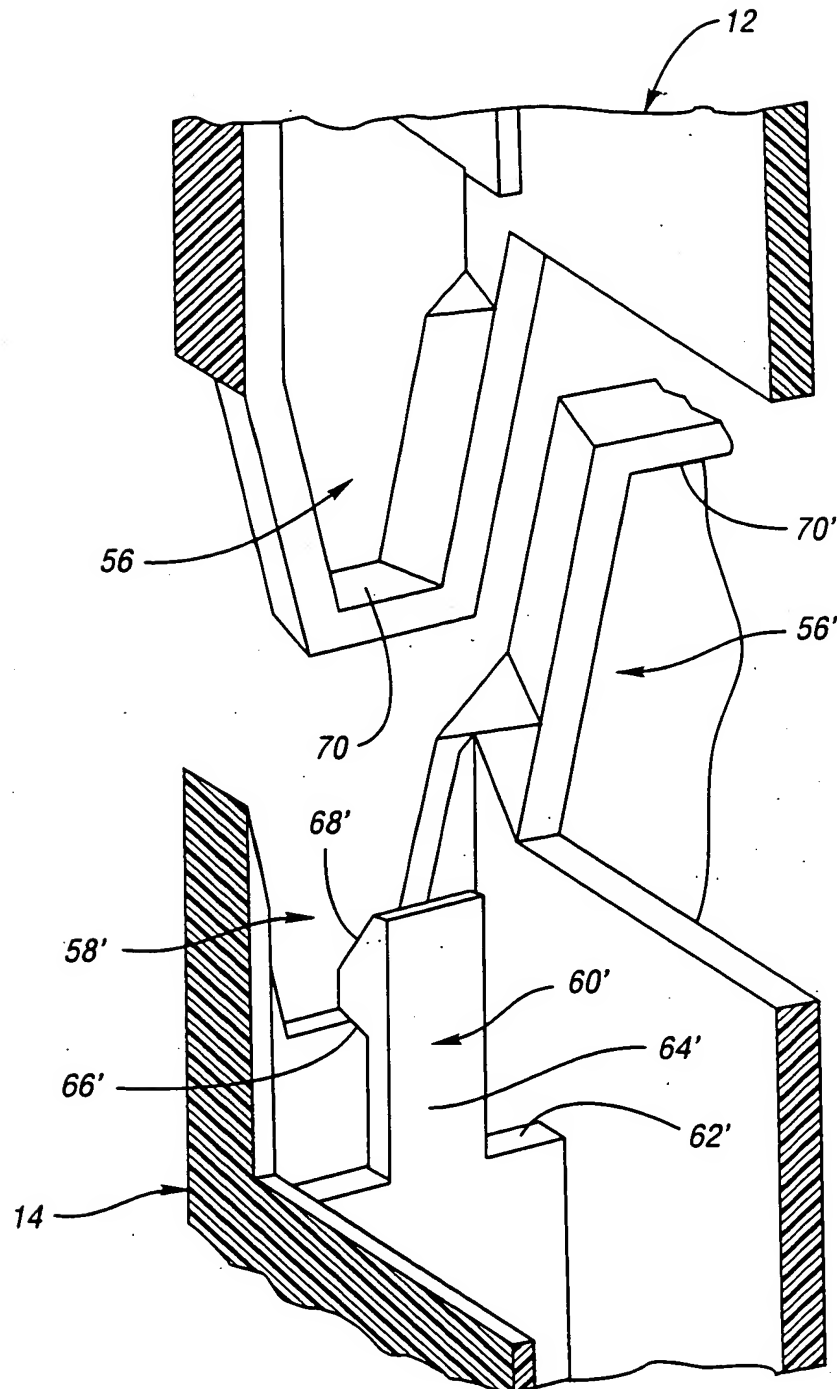
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*Fig. 11*



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*Fig. 13*

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